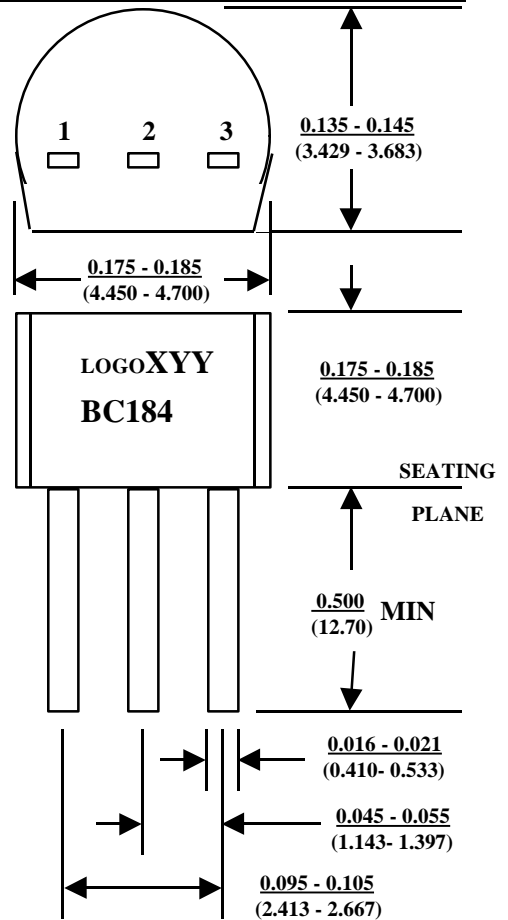
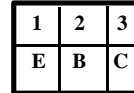


# BC184

## SILICON NPN SMALL SIGNAL TRANSISTOR

$BV_{CEO} \dots 30 \text{ V (Min)}$

$h_{FE} \dots 130 \text{ (Min) @ } V_{CE} = 5.0 \text{ V, } I_C = 100 \text{ mA}$



### ABSOLUTE MAXIMUM RATINGS (NOTE 1)

#### TEMPERATURES

Storage Temperature  $-55 \text{ Degrees C to } 150 \text{ Degrees C}$

Operating Junction Temperature  $150 \text{ Degrees C}$

### POWER DISSIPATION (NOTES 2 & 3)

Total Device Dissipation at  $T_A = 25 \text{ Deg C}$   $625 \text{ mW}$

### VOLTAGES & CURRENT

$V_{CEO}$  Collector to Emitter  $30 \text{ V}$

$V_{CBO}$  Collector to Base  $45 \text{ V}$

$V_{EBO}$  Emitter to Base  $5 \text{ V}$

$I_C$  Collector Current  $500 \text{ mA}$

### ELECTRICAL CHARACTERISTICS (25 Degrees C Ambient Temperature unless otherwise stated)

SYM	CHARACTERISTICS	MIN	MAX	UNITS	TEST CONDITIONS
$BV_{CBO}$	Collector to Base Voltage	45		V	$I_C = 10 \text{ uA}$
$BV_{CEO}$	Collector to Emitter Voltage	30		V	$I_C = 2.0 \text{ mA}$
$BV_{EBO}$	Emitter to Base Voltage	5		V	$I_E = 10 \text{ uA}$
$I_{CBO}$	Collector Cutoff Current		15	nA	$V_{CB} = 30 \text{ V}$
$I_{EBO}$	Collector Cutoff Current		15	nA	$V_{EB} = 4 \text{ V}$
$h_{FE}$	DC Current Gain	100 130			$V_{CE} = 5.0 \text{ V } I_C = 10 \text{ uA}$ $V_{CE} = 5.0 \text{ V } I_C = 100 \text{ mA}$
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage		0.25 0.6	V	$I_C = 10\text{mA } I_B = 0.5\text{mA}$ $I_C = 100\text{mA } I_B = 5.0\text{mA}$
$V_{BE(sat)}$	Base-Emitter Saturation Voltage		1.2	V	$I_C = 100\text{mA } I_B = 5.0\text{mA}$
$V_{BE(on)}$	Base -Emitter On Voltage	0.55	0.7	V	$V_{CE} = 5.0 \text{ V } I_C = 2\text{mA}$

# BC184

## SILICON NPN SMALL SIGNAL TRANSISTOR

**ELECTRICAL CHARACTERISTICS** Con't (25 Degrees C Ambient Temperature unless otherwise stated)

<b>SYM</b>	<b>CHARACTERISTICS</b>	<b>MIN</b>	<b>MAX</b>	<b>UNITS</b>	<b>TEST CONDITIONS</b>
COB	Output Capacitance		5.0	pF	V <sub>CB</sub> = 10 V, f = 1 MHz
f <sub>T</sub>	Current Gain - Bandwidth Product	150		MHz	V <sub>CE</sub> = 5 V    I <sub>C</sub> = 10 mA f = 100 MHz
h <sub>fe</sub>	Small Signal Current Gain	125	500	-	V <sub>CE</sub> = 5 V, I <sub>C</sub> = 2.0 mA, f = 1KHz
NF	Noise Figure		4	dB	V <sub>CE</sub> = 5 V, I <sub>C</sub> = 200 uA, R <sub>g</sub> = 2 Kohms, f = 30Hz to 15KHz

NOTES:

1. These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.
2. These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.
3. These ratings are based on a maximum junction temperature of 150 degrees C.

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FACT™	QS™
FACT Quiet Series™	Quiet Series™
FAST®	SuperSOT™-3
FASTr™	SuperSOT™-6
GTO™	SuperSOT™-8
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## PRODUCT STATUS DEFINITIONS

### Definition of Terms

Datasheet Identification	Product Status	Definition
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